AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1. (original) A semiconductor device, wherein an interlayer dielectric film having Si-H bonds is provided on a base layer including a semiconductor substrate and a silicon carbon nitride film is formed on said interlayer dielectric film.

2. (original) The semiconductor device according to claim 1, wherein an electrically conductive film containing Cu as a main component element is embedded in a trench formed in said interlayer dielectric film and the silicon carbon nitride film is formed on said electrically conductive film.

3. (original) The semiconductor device according to claim 2, wherein said interlayer dielectric film and said electrically conductive film are each formed in a plurality of layers and said silicon carbon nitride film is formed so as to cover said electrically conductive film and said interlayer dielectric film each in a top layer.

4. (original) The semiconductor device according to claim 1, wherein said silicon carbon nitride film has a nitrogen concentration of not less than 10 atm % but less than 35 atm %.

5. (original) The semiconductor device according to claim 2, wherein said silicon carbon nitride film has a nitrogen concentration of not less than 10 atm % but less than 35 atm %.

6. (original) The semiconductor device according to claim 1, wherein said silicon carbon nitride film has a nitrogen concentration of not less than 15 atm % but not more than 30 atm %.

7. (original) The semiconductor device according to claim 2, wherein said silicon carbon nitride film has a nitrogen concentration of not less than 15 atm % but not more than 30 atm %.

8. (original) The semiconductor device according to claim 6, wherein said silicon carbon nitride film contains not less than 22 atm % but not more than 27 atm % Si, not less than 20 atm % but not more than 25 atm % C, and not less than 35 atm % but not more than 45 atm % H.

9. (original) The semiconductor device according to claim 7, wherein said silicon carbon nitride film contains not less than 22 atm % but not more than 27 atm % Si, not less than 20 atm % but not more than 25 atm % C, and not less than 35 atm % but not more than 45 atm % H.

10. (original) The semiconductor device according to claim 4, wherein said silicon carbon nitride film further contains not less than 0.5 atm % but less than 5 atm % O.

11. (original) The semiconductor device according to claim 5, wherein said silicon carbon nitride film further contains not less than 0.5 atm % but less than 5 atm % O.

12. (original) The semiconductor device according to claim 1, wherein said interlayer dielectric film having Si-H bonds is a ladder-type hydrogenated polysiloxane film or a porous ladder-type hydrogenated polysiloxane film.

13. (original) The semiconductor device according to claim 2, wherein said interlayer dielectric film having Si-H bonds is a ladder-type hydrogenated polysiloxane film or a porous ladder-type hydrogenated polysiloxane film.

14. (original) The semiconductor device according to claim 2, wherein a metal nitride film is provided between said interlayer dielectric film and said electrically conductive film containing said Cu as a main component element and a metal film is provided between said electrically conductive film containing said Cu as a main component element and said metal nitride film.

15. (original) The semiconductor device according to claim 2, wherein said electrically conductive film containing Cu as a main component element is a Cu alloy film containing at least one kind selected from the group consisting of Al, Si, Ag, W, Mg, Bi, Zn, Pd, Cd, Au, Hg, Be, Pt, Zr, Ti and Sn.

16. (original) The semiconductor device according to claim 2, wherein said electrically conductive film containing Cu as a main component element is a Cu alloy film containing Si and the Si content is highest on a top surface of the electrically conductive film and gradually decreases with increasing depth in the direction of a bottom surface.

17-32. (canceled)